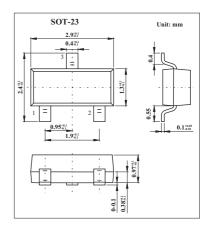
SMD Type Diodes

Silicon Schottky Barrier Diode HRW0302A

Features

- Low forward voltage drop and suitable for high effifiency rectifying.
- MPAK package is suittable for high density surface mounting and high speed assembly.



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	Vrrm	20	V
Average rectified current	lo	300	m A
Non-repetitive peak forward surge current	IFSM (Note 1)	3	А
Junction temperature	Tj	125	$^{\circ}$
Storage temperature	Tstg	-55 to + 125	$^{\circ}\!\mathbb{C}$

Note

1. 10msec sine wave 1 pulse

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF	IF = 200 mA			0.40	V
Reverse current	lr	VR = 20 V			100	μА
Capacitance	С	VR = 0 V, f = 1MHz			100	pF
Thermal resistance	Rth(j-a)	Polyimide board		340		°C/W

■ Marking

Marking	Q11	
iviaikiiig	311	